AMENDED CLAIM SET:

1. (currently amended) A field effect device having a gate dielectric and a channel region, wherein the gate dielectric comprises a germanate material layer and an interlayer disposed between the channel region and the germanate material layer, wherein the interlayer is oxide or oxynitride.

2. (canceled)

3. (currently amended) The field effect device of claim ~~2~~ 1, wherein the germanate material layer has a dielectric constant over 4.

4. (original) The field effect device of claim 3, wherein the germanate material layer has a dielectric constant approximately between 8 and 40.

5. (currently amended) The field effect device of claim ~~2~~ 1, wherein the germanate material layer has a thickness of approximately between 1.5nm and 50nm.

6. (canceled)

7. (currently amended) The field effect device of claim ~~6~~ 1, wherein the interlayer is less than approximately 1nm thick.

8. (canceled)

9. (currently amended) The field effect device of claim 1, wherein the gate dielectric comprising the germanate material layer possesses greater resistance against charge tunneling than a SiO_2 gate dielectric, and a capacitance per unit area of the gate dielectric comprising the germanate material layer is at least as large as the capacitance per unit area of the SiO_2 gate dielectric.

10. (currently amended) The field effect device of claim 1, wherein the germanate material layer is hafnium germanium oxide layer.

11. (original) The field effect device of claim 1, wherein the field effect device is a Si MOS transistor.

12. (original) The field effect device of claim 1, wherein the field effect device is a SiGe-based MOS transistor.

13. (original) The field effect device of claim 1, wherein the field effect device is a Ge MOS transistor.

14. (original) The field effect device of claim 1, wherein the field effect device is a III-V material based MOS transistor.

15. - 25. (canceled)

26. (currently amended) A processor, comprising:

at least one chip, wherein the chip comprises at least one semiconductor field effect device having a gate dielectric and a channel region, wherein the gate dielectric comprises a germanate material layer and an interlayer disposed between the channel region and the germanate material layer, wherein the interlayer is oxide or oxynitride.

27. (original) The processor of claim 26, wherein the processor is a digital processor.

28. (original) The processor of claim 26, wherein the processor comprises at least one analog circuit.